# RGTH50TS65DGC13

### 650V 25A Field Stop Trench IGBT

Datasheet

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	25A
V <sub>CE(sat) (Typ.)</sub>	1.6V
$P_D$	174W

# ● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD (RFN Series)
- 5) Pb free Lead Plating; RoHS Compliant

#### Applications

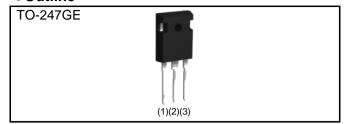
**PFC** 

**UPS** 

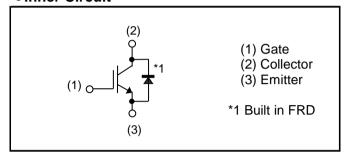
**Power Conditioner** 

ΙH

#### Outline



#### ●Inner Circuit



Packaging Specifications

	Packaging	Tube		
		Reel Size (mm)	-	
Tur	20	Tape Width (mm)	-	
Туре	Je	Basic Ordering Unit (pcs)	600	
		Packing code	C13	
	Marking	RGTH50TS65D		

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
	T <sub>C</sub> = 25°C	I <sub>C</sub>	50	А
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	25	А
Pulsed Collector Current	I <sub>CP</sub> *1	I <sub>CP</sub> *1 100		
Diode Forward Current	T <sub>C</sub> = 25°C	I <sub>F</sub>	35	А
	T <sub>C</sub> = 100°C	I <sub>F</sub>	20	А
Diode Pulsed Forward Current		I <sub>FP</sub> *1	100	А
Dower Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	174	W
Power Dissipation	T <sub>C</sub> = 100°C	$P_{D}$	87	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax.</sub>

#### ●Thermal Resistance

Parameter	Cymbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.86	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.28	°C/W

## ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai iletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_C = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	1	-	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, \ V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 17.5 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 25A, V_{GE} = 15V$ $T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$	-	1.6 2.1	2.1 -	V

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Unit		
i didilielei			Min.	Тур.	Max.	Offic
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	1410	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	57	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	22	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V	-	49	-	
Gate - Emitter Charge	$Q_ge$	I <sub>C</sub> = 25A	-	15	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	19	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 25A, V_{CC} = 400V$	-	27	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	38	-	20
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	94	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	50	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 25A, V_{CC} = 400V$	-	27	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_{G} = 10\Omega$	-	38	-	20
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	107	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	65	-	
		I <sub>C</sub> = 100A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650 V, V_{GE} = 15 V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Datasheet

## **•FRD Electrical Characteristics** (at $T_j = 25$ °C unless otherwise specified)

Dovometer	Symbol	Conditions	Values			Unit
Parameter			Min.	Тур.	Max.	Unit
Diode Forward Voltage	$V_F$	$I_F = 20A$ $T_i = 25$ °C	_	1.45	1.9	V
	•	T <sub>j</sub> = 175°C	-	1.25	-	
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_F = 20A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 25^{\circ}C$	-	58	-	ns
Diode Peak Reverse Recovery Current	l <sub>rr</sub>		-	6.3	-	А
Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	0.20	-	μC
Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A	-	256	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>	$V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 175^{\circ}C$	-	10.4	-	А
Diode Reverse Recovery Charge	$Q_{rr}$		-	1.35	-	μC

Fig.1 Power Dissipation vs. Case Temperature

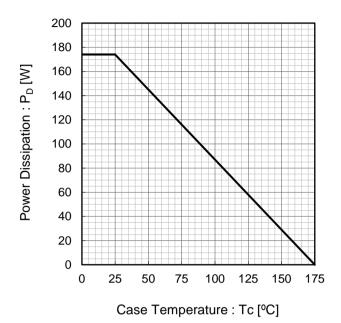


Fig.2 Collector Current vs. Case Temperature

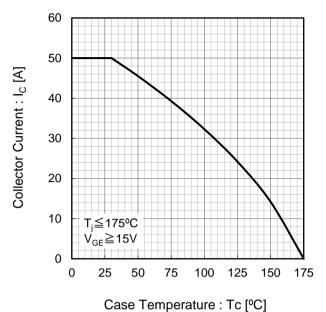


Fig.3 Forward Bias Safe Operating Area

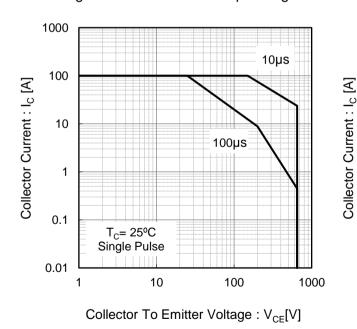
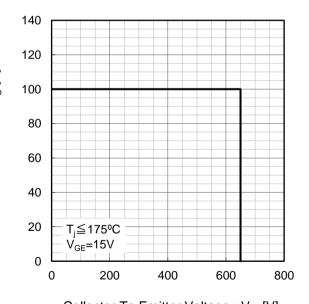


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.5 Typical Output Characteristics

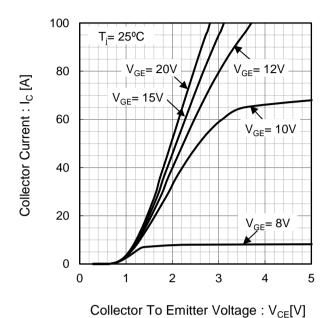
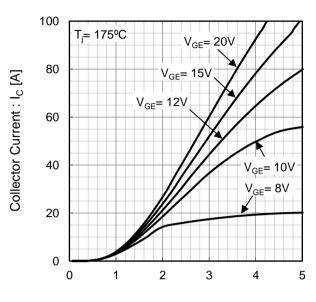


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.7 Typical Transfer Characteristics

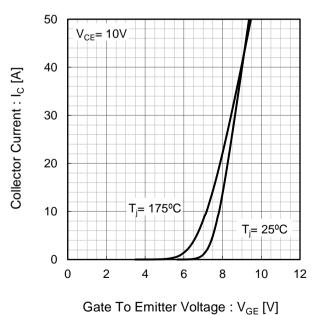
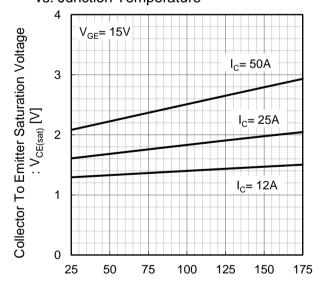
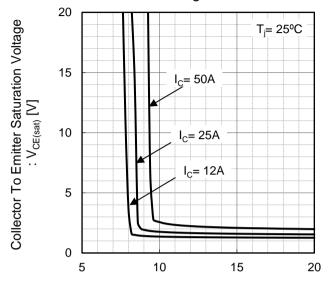


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



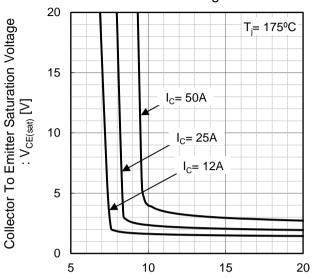
Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



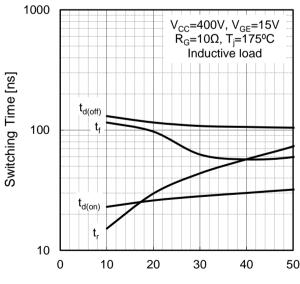
Gate To Emitter Voltage: V<sub>GE</sub> [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



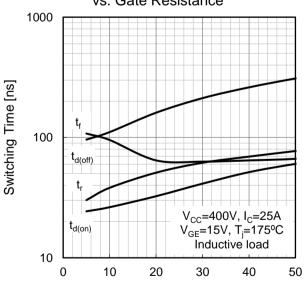
Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current



Collector Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance :  $R_G[\Omega]$ 

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$ 0.1  $E_{on}$  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 30 40 50 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] 1  $E_{off}$ 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=25A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] 100 Coes Cres 10 f=1MHz  $V_{GE}=0V$ T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage :  $V_{CE}[V]$ 

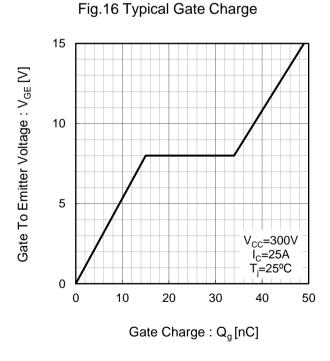


Fig.17 Typical Diode Forward Current vs. Forward Voltage

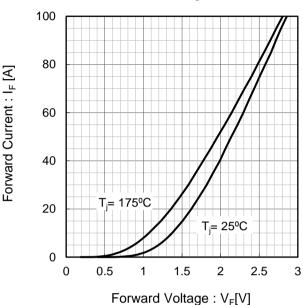


Fig.18 Typical Diode Reverse Recovery Time vs. Forward Current

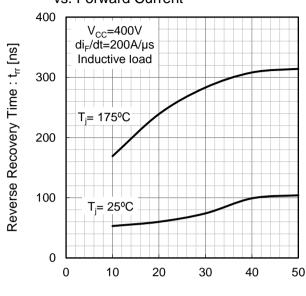


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

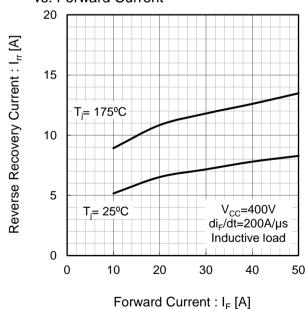


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current

Forward Current : I<sub>F</sub> [A]

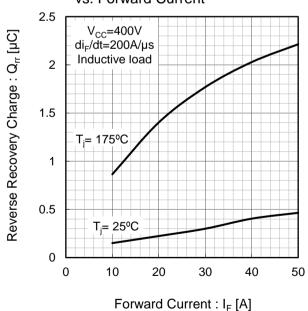


Fig.21 IGBT Transient Thermal Impedance

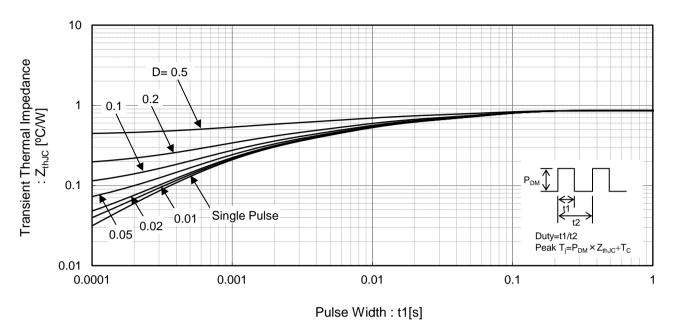
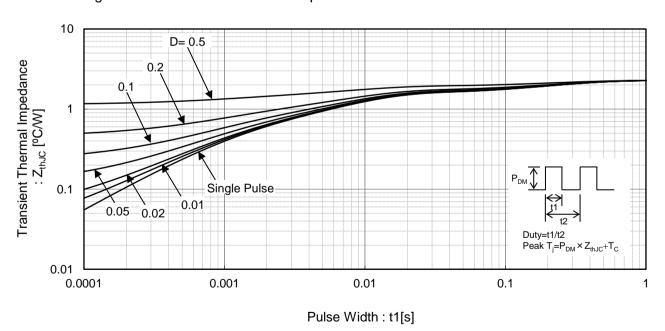


Fig.22 Diode Transient Thermal Impedance



### ●Inductive Load Switching Circuit and Waveform

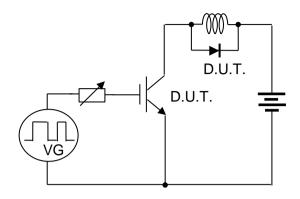


Fig.23 Inductive Load Circuit

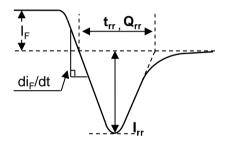


Fig.25 Diode Reverce Recovery Waveform

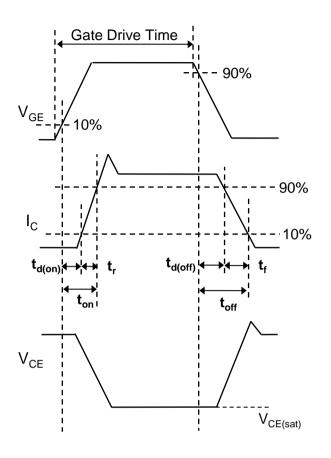


Fig.24 Inductive Load Waveform

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